

N-channel TrenchMOS logic level FET 28 July 2016

**Product data sheet** 

### 1. General description

Logic level N-channel MOSFET in a SOT404 package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

### 2. Features and benefits

- AEC Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True logic level gate with VGS(th) rating of greater than 0.5V at 175 °C

### 3. Applications

- 12 V Automotive systems
- Motors, lamps and solenoid control
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

### 4. Quick reference data

Table 1. Quie	ck reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	60	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 5 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	-	56	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	-	96	W
Static characte	eristics						
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 5 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 25 °C; <u>Fig. 11</u>		-	11.5	14	mΩ
Dynamic characteristics							
Q <sub>GD</sub>	gate-drain charge	V <sub>GS</sub> = 5 V; I <sub>D</sub> = 15 A; V <sub>DS</sub> = 48 V; <u>Fig. 13; Fig. 14</u>		-	6.7	-	nC

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# 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D
2	D	drain		
3	S	source		G-UITA
mb	D	mounting base; connected to drain	D2PAK (SOT404)	mbb076 S

# 6. Ordering information

Table 3. Ordering information							
Type number	Package						
	Name	Description	Version				
BUK9614-60E	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404				

### 7. Marking

Table 4. Marking codes	
Type number	Marking code
BUK9614-60E	BUK9614-60E

## 8. Limiting values

#### Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	60	V
V <sub>DGR</sub>	drain-gate voltage	R <sub>GS</sub> = 20 kΩ		-	60	V
V <sub>GS</sub>	gate-source voltage	T <sub>j</sub> ≤ 175 °C; DC		-10	10	V
		$T_j \le 175 \text{ °C}; \text{ Pulsed}$	[1][2]	-15	15	V
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	96	W
I <sub>D</sub>	drain current	T <sub>mb</sub> = 25 °C; V <sub>GS</sub> = 5 V; <u>Fig. 2</u>		-	56	А
		T <sub>mb</sub> = 100 °C; V <sub>GS</sub> = 5 V; <u>Fig. 2</u>		-	40	А
I <sub>DM</sub>	peak drain current	$T_{mb}$ = 25 °C; pulsed; $t_p \le 10 \ \mu$ s; Fig. 3		-	224	А
T <sub>stg</sub>	storage temperature			-55	175	°C
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Symbol	Parameter	Conditions		Min	Мах	Unit
Tj	junction temperature			-55	175	°C
Source-dra	ain diode					
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	[3]	-	56	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^\circ C$		-	224	А
Avalanche	ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$\begin{split} & {\sf I}_{D} = 56 \; {\sf A}; \; {\sf V}_{sup} \le 60 \; {\sf V}; \; {\sf R}_{GS} = 50 \; \Omega; \\ & {\sf V}_{GS} = 5 \; {\sf V}; \; {\sf T}_{j(init)} = 25 \; ^{\circ}{\sf C}; \; unclamped; \\ & {\sf Fig. 4} \end{split}$	[4][5]	-	39	mJ

- Accumulated pulse duration up to 50 hours delivers zero defect ppm [1]
- [2] Significantly longer life times are achieved by lowering  $T_{j}$  and or  $V_{\text{GS}}$
- [3] Continuous current is limited by package.
- Single-pulse avalanche rating limited by maximum junction temperature of 175 °C. Refer to application note AN10273 for further information. [4]
- [5]

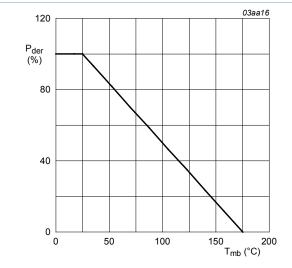
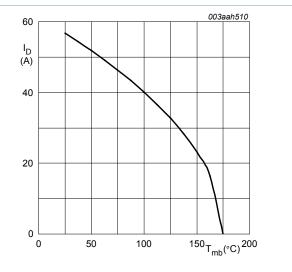


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

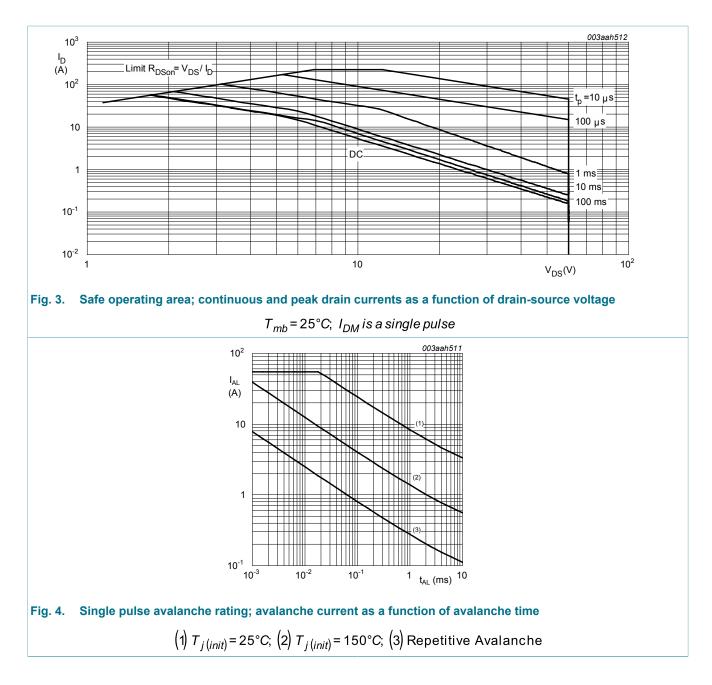


Continuous drain current as a function of Fig. 2. mounting base temperature

 $V_{GS} \ge 5V$ 

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### 9. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. <u>5</u>	-	-	1.56	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	minimum footprint ; mounted on a printed-circuit board	-	50	-	K/W

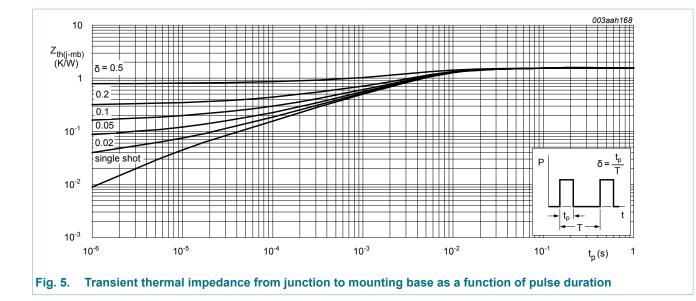
#### Table 6. Thermal characteristics

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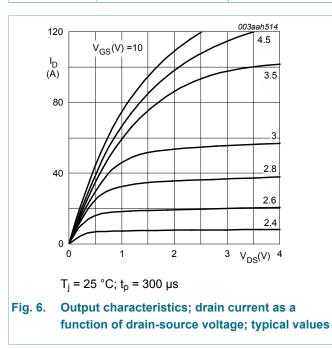
## **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics					
V <sub>(BR)DSS</sub>	drain-source	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = 25 °C	60	-	-	V
	breakdown voltage	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = -55 °C	54	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ Fig. 9; Fig. 10	1.4	1.7	2.1	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 9	-	0.5 0.02 1 - 500	2.45	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ Fig. 9	0.5	-	-	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 60 \text{ V}; \text{ V}_{GS} = 0 \text{ V}; \text{ T}_{j} = 25 \text{ °C}$	-	0.02	- 2.1 2.45 - 1 500	μA
		V <sub>DS</sub> = 60 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C	-	-	500	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = 10 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	2	- 2.1 2.45 - 1 500 100 14 12.8 31 -	nA
		$V_{GS}$ = -10 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state	V <sub>GS</sub> = 5 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 25 °C; <u>Fig. 11</u>	-	11.5	- 2.1 2.45 2.45 - 1 500 100 100 14 12.8 31	mΩ
	resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 25 °C; Fig. 11	-	10.3	12.8	mΩ
		V <sub>GS</sub> = 5 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 175 °C; Fig. 12; Fig. 11	- ,	31	mΩ	
Dynamic cl	naracteristics	· ·	1			
Q <sub>G(tot)</sub>	total gate charge	$I_D$ = 15 A; $V_{DS}$ = 48 V; $V_{GS}$ = 5 V;	-	20.5	-	nC
Q <sub>GS</sub>	gate-source charge	Fig. 13; Fig. 14	-	4	-	nC

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Q <sub>GD</sub>	gate-drain charge		-	6.7	-	nC
C <sub>iss</sub>	input capacitance	$V_{GS}$ = 0 V; $V_{DS}$ = 25 V; f = 1 MHz;	-	1988	2651	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 15</u>	-	196	235	pF
C <sub>rss</sub>	reverse transfer capacitance	$V_{DS}$ = 45 V; R <sub>L</sub> = 3 Ω; V <sub>GS</sub> = 5 V; R <sub>G(ext)</sub> = 5 Ω	-	114	156	pF
t <sub>d(on)</sub>	turn-on delay time		-	16.9	-	ns
t <sub>r</sub>	rise time		-	22.4	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	35.7	-	ns
t <sub>f</sub>	fall time		-	22.9	-	ns
L <sub>D</sub>	internal drain inductance	from upper edge of drain mounting base to center of die	-	2.5	-	nH
L <sub>S</sub>	internal source inductance	from source lead to source bonding pad	-	7.5	-	nH
Source-dra	in diode					
V <sub>SD</sub>	source-drain voltage	$I_{S}$ = 15 A; $V_{GS}$ = 0 V; $T_{j}$ = 25 °C; <u>Fig. 16</u>	-	0.83	1.2	V
t <sub>rr</sub>	reverse recovery time	from upper edge of drain mounting base to center of die from source lead to source bonding pad	-	22.3	-	ns
Q <sub>r</sub>	recovered charge	V <sub>DS</sub> = 25 V	-	20.9	-	nC



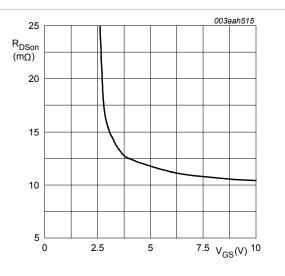
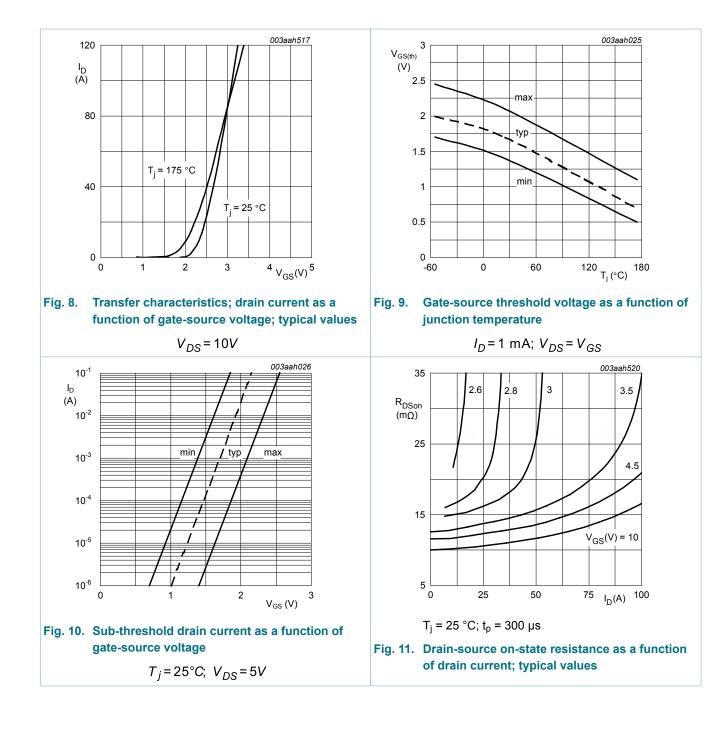


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

 $T_j = 25^{\circ}C; I_D = 15A$ 

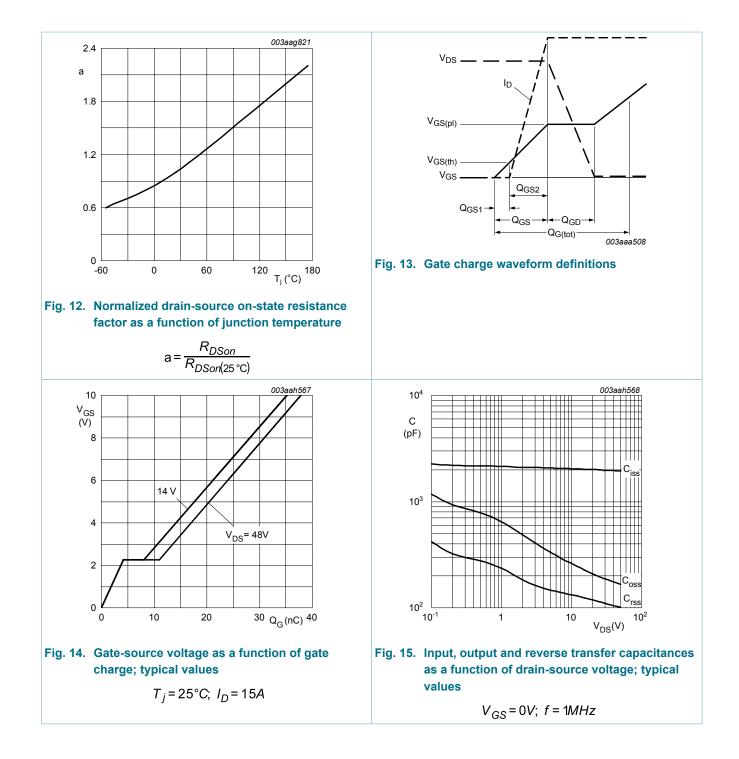
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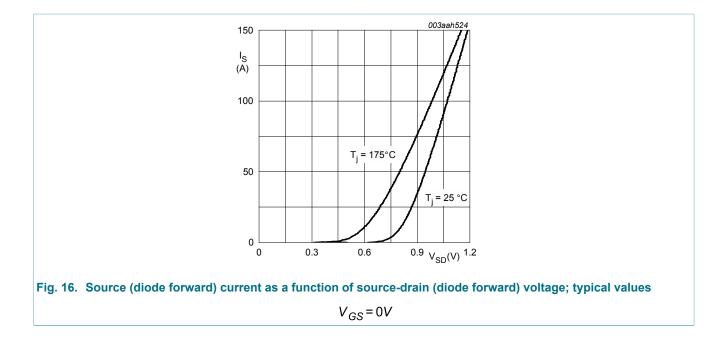
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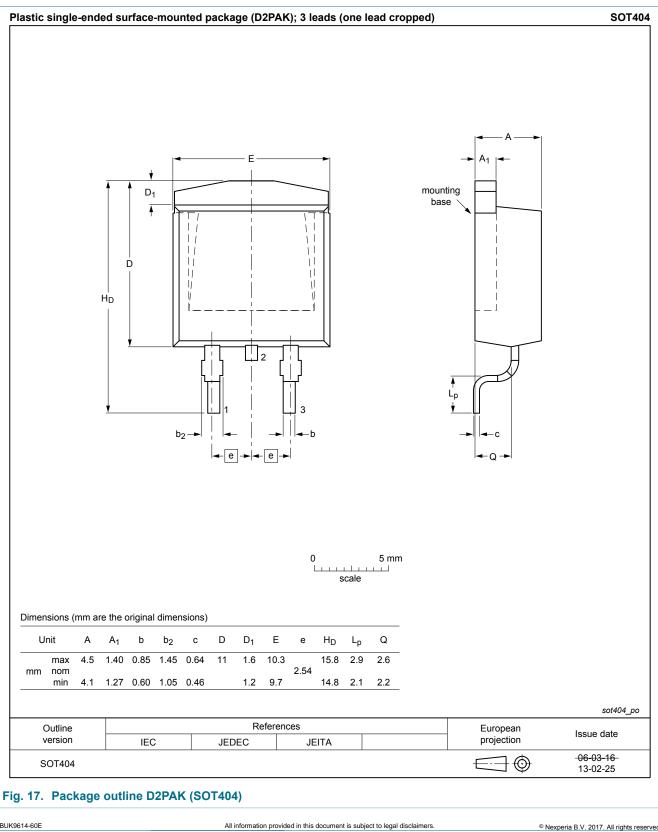
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### 11. Package outline



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### 12. Legal information

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Document status [1][2]	Product status [ <u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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